

AMENDMENTS

Please amend the above-identified patent application as follows:

IN THE CLAIMS:

Please amend Claims 7, 8 and 9 as follows:

7. (Amended) A bottom gate thin film transistor comprising an active layer including a polycrystalline silicon film where a drain, a source and a channel are defined, grain sizes of the drain and source being greater than a grain size of the channel.

8. (Amended) A thin film transistor comprising:
an insulator substrate;
a gate electrode located on the insulator substrate;
an insulator film provided on the insulator substrate and the gate electrode; and
a polycrystalline silicon film located on the insulator film, a channel defined in a first portion of the polycrystalline silicon film over the gate electrode, a drain and a source defined in second and third portions of the polycrystalline silicon film over the insulator substrate, grain sizes of the drain and source being greater than a grain size of the channel.

9. (Amended) The thin film transistor according to claim 8, wherein the grain size of the channel is set large enough to provide a desired on current of the thin film transistor.